

DB3J406N0L

Silicon epitaxial planar type

For high speed switching circuits

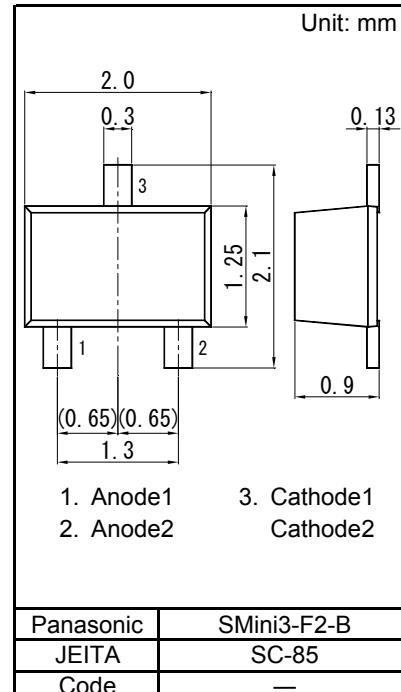
■ Features

- Small reverse current IR
- Short reverse recovery time trr
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 5V

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Reverse voltage	VR	40	V
Repetitive peak reverse voltage	VRRM	40	V
Forward current	IF	100	mA
		75	mA
Peak forward current	IFM	300	mA
		225	mA
Non-repetitive peak forward surge current ^{*1}	IFSM	1	A
Junction temperature	Tj	125	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +125	°C

Note: *1 The peak-to-peak value in one cycle of 50 Hz sine wave (non-repetitive)

Internal Connection

